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FAN54040 — FAN54047 USB-OTG, 1.55 A, Li-Ion Switching Charger with Power Path and 2.3 A Production Test Support

Features

- Fully Integrated, High-Efficiency Charger for Single-Cell Li-Ion and Li-Polymer Battery Packs
- Power Path Circuit Ensures Fast System Startup with a Dead Battery when VBUS is Connected
- 1.55 A Maximum Charge Current
- Float Voltage Accuracy:
 - ±0.5% at 25°C
 - ±1% from 0 to 125°C
- ±5% Input and Charge Current Regulation Accuracy
- Temperature-Sense Input Prevents Auto-Charging for JEITA Compliance
- Thermal Regulation and Shutdown
- 4.2 V at 2.3 A Production Test Mode
- 5 V, 500 mA Boost Mode for USB OTG
- 28 V Absolute Maximum Input Voltage
- 6 V Maximum Input Operating Voltage
- Programmable through High-Speed I²C Interface (3.4 Mb/s) with Fast Mode Plus Compatibility
 - Input Current
 - Fast-Charge / Termination Current
 - Float Voltage
 - Termination Enable
- 3 MHz Synchronous Buck PWM Controller with Wide Duty Cycle Range
- Small Footprint 1 µH External Inductor
- Safety Timer with Reset Control
- Dynamic Input Voltage Control
- Very Low Battery Current when Charger Inactive

Applications

- Cell Phones, Smart Phones, PDAs
- Tablet, Portable Media Players
- Gaming Device, Digital Cameras

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Description

The FAN5404X family includes I^2C controlled 1.55 A USBcompliant switch-mode chargers with power path operation and USB OTG boost operation. Integrated with the charger, the IC supports production test mode, which provides 4.2 V at up to 2.3 A to the system.

To facilitate fast system startup, the IC includes a power path circuit, which disconnects the battery from the system rail, ensuring that the system can power up quickly following a VBUS connection. The power path circuit ensures that the system rail stays up when the charger is plugged in, even if the battery is dead or shorted.

The charging parameters and operating modes are programmable through an I^2C Interface that operates up to 3.4 Mbps. The charger and boost regulator circuits switch at 3 MHz to minimize the size of external passive components.

The FAN5404X provides battery charging in three phases: conditioning, constant current, and constant voltage. The integrated circuit automatically restarts the charge cycle when the battery falls below a voltage threshold. If the input source is removed, the IC enters a high-impedance mode blocking battery current from leaking to the input. Charge status is reported back to the host through the I²C port.

Dynamic input voltage control prevents a weak adapter's voltage from collapsing, ensuring charging capability from such adapters.

The FAN5404X is available in a 25-bump, 0.4 mm pitch, WLCSP package.

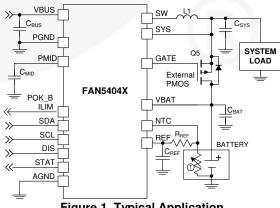


Figure 1. Typical Application

FAN54040 - FAN54047-
047— USB-C
— USB-OTG,1.55 A Li
-Ion Switchin
g Charger wit
ith Power Path
r Path and 2.3 A P
Production Test S
est Support

Ordering Information

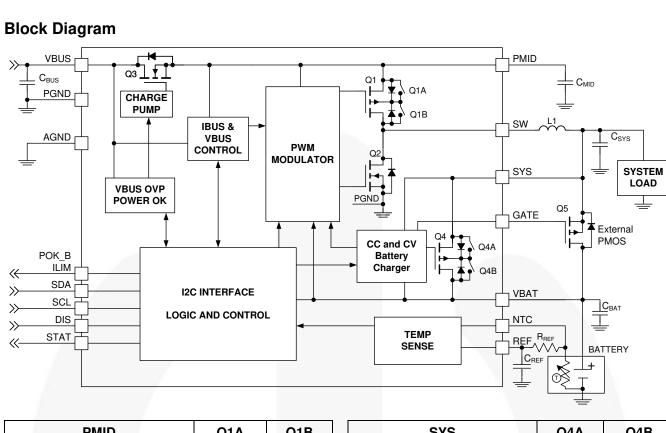
Part Number	Temperature Range	Package	PN Bits: IC_INFO[5:3]	Packing Method
FAN54040UCX			000	
FAN54041UCX	-40 to 85°C Chip-Scale Packag		001	
FAN54042UCX ⁽¹⁾		25-Bump, Wafer-Level Chip-Scale Package (WLCSP), 0.4 mm Pitch	010	Tono and Dool
FAN54045UCX ⁽¹⁾			101	Tape and Reel
FAN54046UCX ⁽¹⁾			110	
FAN54047UCX			110	

Note:

1. Contact Fairchild Sales for availability.

Table 1. Feature Comparison Summary

Part Number	Slave Address	Automatic Charge	Battery Absent Behavior	E1 Pin
FAN54040	1101011	Yes	Off	POK_B
FAN54041	1101011	No	Off	POK_B
FAN54042	1101011	Yes	On	POK_B
FAN54045	1101011	No	Off	ILIM
FAN54046	1101011	No	On	ILIM
FAN54047	1101011	Yes	On	ILIM



PMID	Q1A	Q1B
Greater than V _{BAT}	ON	OFF
Less than V _{BAT}	OFF	ON

SYS	Q4A	Q4B
Greater than V _{BAT}	ON	OFF
Less than V _{BAT}	OFF	ON

Figure 2. IC and System Block Diagram

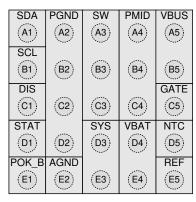
Table 2. Recommended External Components

Component	Description	Vendor	Parameter	Тур.	Unit
1.4	1 11 000/ 0.0 1 0010	Taiyo Yuden MAKK2016T1R0M	L	1.0	μH
L1	1 μH, 20%, 2.2 A, 2016	or Equivalent	DCR (Series R)	75	mΩ
$C_{\text{BAT}}, C_{\text{SYS}}$	10 μF, 20%, 6.3 V, X5R, 0603	Murata: GRM188R60J106M TDK: C1608X5R0J106M	С	10	μF
C _{MID}	4.7 μF, 10%, 6.3 V, X5R, 0603	Murata: GRM188R60J475K TDK: C1608X5R0J475K	C ⁽²⁾	4.7	μF
C _{BUS,}	1.0 μF, 10%, 25 V, X5R, 0603	Murata GRM188R61E105K TDK:C1608X5R1E105M	С	1.0	μF
Q5	PMOS,12 V, 16 mΩ, MLP2x2	Fairchild FDMA905P	R _{DS(ON)}	16	mΩ
C _{REF}	1 μF, 10%, 6.3 V, X5R, 0402		С	1.0	μF

Note:

2. 6.3 V rating is sufficient for C_{MID} since PMID is protected from over-voltage surges on VBUS by Q3.

Pin Configuration



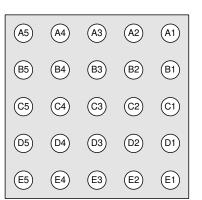


Figure 3. Top View

Figure 4. Bottom View

Pin Definitions

Pin #	Name	Description
A1	SDA	I ² C Interface Serial Data. This pin should not be left floating.
B1	SCL	I ² C Interface Serial Clock. This pin should not be left floating.
C1	DIS	Disable . If this pin is held HIGH, Q1 and Q3 are turned off, creating a HIGH Z condition at VBUS and the PWM converter is disabled.
D1	STAT	Status . Open-drain output indicating charge status. The IC pulls this pin LOW when charge is in progress; can be used to signal the host processor when a fault condition occurs.
E1	POK_B	Power OK (FAN54040-2) . Open-drain output that pulls LOW when VBUS is plugged in and the battery has risen above V_{LOWV} . This signal is used to signal the host processor that it can begin to draw significant current.
E1	ILIM	Input Current Limit (FAN54045-7) . Controls input current limit in Auto-Charge Mode. When LOW, input current is limited to 100 mA maximum. When HIGH, input current is limited to 500 mA. In 32-Second Mode, the input current limit is set by the I _{BUSLIM} bits.
A2 – D2	PGND	Power Ground . Power return for gate drive and power transistors. The connection from this pin to the bottom of C_{MID} should be as short as possible.
E2	AGND	Analog Ground. All IC signals are referenced to this node.
A3 – C3	SW	Switching Node. Connect to output inductor.
D3 – E3	SYS	System Supply . Output voltage of the switching charger and input to the power path controller. Bypass SYS to PGND with a 10 μ F capacitor.
A4 – C4	PMID	Power Input Voltage . Power input to the charger regulator, bypass point for the input current sense. Bypass with a minimum of a 4.7 μ F, 6.3 V capacitor to PGND.
D4 – E4	VBAT	Battery Voltage . Connect to the positive (+) terminal of the battery pack. Bypass with a 10 μ F capacitor to PGND. VBAT is a power path connection.
A5 – B5	VBUS	Charger Input Voltage and USB-OTG output voltage. Bypass with a 1 µF capacitor to PGND.
C5	GATE	External MOSFET Gate . This pin controls the gate of an external P-channel MOSFET transistor used to augment the internal ideal diode. The source of the P-channel MOSFET should be connected to SYS and the drain should be connected to VBAT.
D5	NTC	Thermistor input . The IC compares this node with taps on a resistor divider from REF to inhibit auto- charging when the battery temperature is outside of permitted fast-charge limits.
E5	REF	Reference Voltage. REF is a 1.8 V regulated output.

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameter				Max.	Unit
V	Voltage on VDLIC Din	Continuous		-0.3	00.0	v
V _{BUS}	Voltage on VBUS Pin	Pulsed, 100 ms Maximum Non-Repetitiv			28.0	v
M	Voltage on PMID Voltage Pin			-0.3	7.0	v
Vı	Voltage on SW, SYS, VBAT, ST	oltage on SW, SYS, VBAT, STAT, DIS Pins			7.0	v
Vo	Voltage on Other Pins		-0.3	6.5 ⁽³⁾	V	
dV _{BUS} dt	Maximum V_{BUS} Slope Above 5.5 V when Boost or Charger Active				4	V/µs
	Electrostatic Discharge	Human Body Model	per JESD22-A114	20	000	v
ESD	Protection Level	Charged Device Model per JESD22-C101		500		v
ESD		USB Connector	Air Gap	1	15	
	IEC 61000-4-2 System ESD ⁽⁴⁾	Pins (V_{BUS} to GND)	Contact	8		kV
TJ	Junction Temperature			-40	+150	°C
T _{STG}	Storage Temperature			-65	+150	°C
TL	Lead Soldering Temperature, 10	Seconds			+260	°C

Note:

3. Lesser of 6.5 V or V_1 + 0.3 V.

4. Guaranteed if $C_{BUS} \ge 1 \ \mu F$ and $C_{MID} \ge 4.7 \ \mu F$.

Recommended Operating Conditions

The Recommended Operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications. Fairchild does not recommend exceeding them or designing to absolute maximum ratings.

Symbol	Parameter		Min.	Max.	Unit
V _{BUS}	Supply Voltage		4	6	V
V _{BAT(MAX)}	Maximum Battery Voltage when Boost enabled			4.5	V
	Negative VBUS Slew Rate during VBUS Short Circuit,	T _A <u><</u> 60°C		4	M/me
dt	$C_{MID} \leq 4.7 \ \mu F$, see VBUS Short While Charging	$T_A \ge 60^{\circ}C$		2	V/µs
TA	Ambient Temperature		-30	+85	°C
TJ	Junction Temperature (see Thermal Regulation and Prote	ection section)	-30	+120	°C

Thermal Properties

Junction-to-ambient thermal resistance is a function of application and board layout. This data is measured with four-layer 2s2p boards in accordance to JEDEC standard JESD51. Special attention must be paid not to exceed junction temperature $T_{J(max)}$ at a given ambient temperature T_A . For measured data, see Table 18.

Symbol	Parameter		Unit
θ _{JA}	Junction-to-Ambient Thermal Resistance (see also Figure 18)	50	°C/W
θ_{JB}	Junction-to-PCB Thermal Resistance	20	°C/W

Electrical Specifications

Unless otherwise specified: according to the circuit of Figure 1; recommended operating temperature range for T_J and T_A ; V_{BUS} =5.0 V; HZ_MODE; OPA_MODE=0; (Charge Mode); SCL, SDA=0 or 1.8 V; and typical values are for T_J =25°C.

Symbol	Parameter	Conditi	ons	Min.	Тур.	Max.	Unit
Power Supp	lies			•			
		$V_{BUS} > V_{BUS(min)}, PWN$	1 Switching		10		mA
I _{VBUS}	VBUS Current	$V_{BUS} > V_{BUS(min)}; V_{BAT}$ I_{BUSLIM} =100 mA	> V _{OREG}		2.5		mA
		$\begin{array}{l} 0^{\circ}C < T_{J} < 85^{\circ}C, \ HZ_MODE=1 \\ V_{BAT} < V_{LOWV}, \ 32S \ Mode, \ I_{REG}=0 \end{array}$				280	μA
I _{BAT_HZ}	Battery Discharge Current in High- Impedance Mode	DIS=1, or HZ_MODE V _{BUS} =0, 5 V or Floatin			<1	10	μA
I _{BUS_HZ}	Battery Leakage Current to V_{BUS} in High-Impedance Mode	DIS=1, or HZ_MODE V _{BUS} Shorted to Grou		-5.0	-0.2		μΑ
Charger Vol	tage Regulation						
	Charge Voltage Range			3.5		4.4	V
VOREG		T _A =25°C		-0.5		+0.5	%
	Charge Voltage Accuracy	T _J =0 to 125°C		-1		+1	%
Charging Cu	urrent Regulation						
			IO_LEVEL=0	550		1550	mA
I _{OCHRG}	Output Charge Current Range	$V_{LOWV} < V_{BAT} < V_{OREG}$	IO_LEVEL=1	290	340	390	mA
	Charge Current Accuracy	IO_LEVEL=0		-5		+5	%
Weak Batter							1
V _{LOWV}	Weak Battery Threshold Range			3.4		3.7	V
	Weak Battery Threshold Accuracy			-5		+5	%
	Weak Battery Deglitch Time	Rising Voltage, 2 mV Overdrive			30		ms
Logic Levels	s : DIS, SDA, SCL						
VIH	High-Level Input Voltage			1.05			V
VIL	Low-Level Input Voltage					0.4	V
l _{iN}	Input Bias Current	Input Tied to GND or	V _{BUS}		0.01	1.00	μA
Charge Tern	nination Detection	, ·		1			
	Termination Current Range	$V_{BAT} > V_{OREG} - V_{RCH}$,	V _{BUS} > V _{SLP}	50		400	mA
		I_{TERM} Setting $\leq 100 \text{ mA}$		-15		+15	
(TERM)	Termination Current Accuracy	I _{TERM} Setting ≥ 200 m		-5		+5	%
	Termination Current Deglitch Time				30		ms
Power Path	(Q4) Control						
			IO LEVEL=1	290	340	390	mA
I _{LIN}	Power Path Max. Charge Current	I _{BUSLIM} > 01, I _{OCHARGE} ≤ 02	IO_LEVEL=0	400	450	510	mA
		I _{BUSLIM} > 01, I _{OCHARGE} > 02	IO_LEVEL=0	650	725	800	mA
\/	VBAT to SYS Threshold for Q4 and	(SYS-VBAT) Falling		-6	-5	-3	mV
VTHSYS	Gate Transition While Charging	(SYS-VBAT) Rising		-1	+1	2	mV
Production -	Test Mode						
$V_{\text{BAT}(\text{PTM})}$	Production Test Output Voltage	$1 \text{ mA} < I_{BAT} < 2 \text{ A}, V_{BT}$	_{JS} =5.5 V	4.116	4.200	4.284	V
I _{BAT(PTM)}	Production Test Output Current	20% Duty with Max. Period 10 ms		2.3			Α

Continued on the following page...

Electrical Specifications (Continued)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Input Power	Source Detection			I.	1	
T1	T1 (0°C) Temperature Threshold		71.9	73.9	75.9	
T2	T1 (10°C) Temperature Threshold		62.6	64.6	66.6	% of
Т3	T1 (45°C) Temperature Threshold		31.9	32.9	34.9	V_{REF}
T4	T1 (60°C) Temperature Threshold		21.3	23.3	25.3	
Input Power	Source Detection				1	
V _{IN(MIN)1}	VBUS Input Voltage Rising	To Initiate and Pass VBUS Validation		4.29	4.42	V
V _{IN(MIN)2}	Minimum VBUS during Charge	During Charging		3.71	3.94	V
tvbus_valid	VBUS Validation Time			30		ms
V _{BUS} Control	l Loop				1	
VBUSLIM	VBUS Loop Setpoint Accuracy		-3		+3	%
Input Curren	nt Limit			1		
	Charger Input Current Limit	I _{BUSLIM} Set to 100 mA	88	93	98	
I _{BUSLIM}	Threshold	I _{BUSLIM} Set to 500 mA	450	475	500	mA
VREF Bias Ge	enerator					
	Bias Regulator Voltage	$V_{BUS} > V_{IN(MIN)}$		1.8		V
V _{REF}	Short-Circuit Current Limit			2.5		mA
Battery Rech	harge Threshold			1		
	Recharge Threshold	Below V _(OREG)	100	120	150	mV
V _{RCH}	Deglitch Time	V _{BAT} Falling Below V _{RCH} Threshold		130		ms
STAT, POK_	B Output			1		
V _{STAT(OL)}	STAT Output Low	I _{STAT} =10 mA			0.4	V
I _{STAT(OH)}	STAT High Leakage Current	V _{STAT} =5 V			1	μA
Battery Dete			1			<u> </u>
IDETECT	Battery Detection Current before Charge Done (Sink Current) ⁽⁵⁾	Begins after Termination Detected		-0.8		mA
tDETECT	Battery Detection Time	and $V_{BAT} \leq V_{OREG} - V_{RCH}$		262	1	ms
Sleep Comp	arator					
V _{SLP}	Sleep-Mode Entry Threshold, V _{BUS} – V _{BAT}	2.3 V \leq V _{BAT} \leq V _{OREG} , V _{BUS} Falling	0	0.04	0.10	V
Power Switc	hes (see Figure 2)				1	
	Q3 On Resistance (VBUS to PMID)	I _{IN(LIMIT)} =500 mA	1	180	250	
Р	Q1 On Resistance (PMID to SW)			130	225	mΩ
$R_{DS(ON)}$	Q2 On Resistance (SW to GND)			150	225	1
	Q4 On Resistance (SYS to VBAT)	V _{BAT} =4.2 V		70	100	mΩ
I _{SYNC}	Synchronous to Non-Synchronous Current Cut-Off Threshold ⁽⁶⁾	Low-Side MOSFET (Q2) Cycle-by- Cycle Current Limit		140		mA

Unless otherwise specified: according to the circuit of Figure 1; recommended operating temperature range for T_J and T_A ; $V_{BUS}=5.0 \text{ V}$; HZ_MODE; OPA_MODE=0; (Charge Mode); SCL, SDA=0 or 1.8 V; and typical values are for $T_J=25^{\circ}$ C.

Continued on the following page...

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
•	M Modulator					
f _{SW}	Oscillator Frequency		2.7	3.0	3.3	MHz
D _{MAX}	Maximum Duty Cycle				100	%
D _{MIN}	Minimum Duty Cycle			0		%
Boost Mode	Operation (OPA_MODE=1, HZ_MOD	DE=0)				1
V _{BOOST} Boost Output Voltage at VBUS		2.5 V < V _{BAT} < 4.5 V, I _{LOAD} from 0 to 200 mA	4.80	5.07	5.20	v
V _{BOOST}	Boost Output Voltage at VBOS	$3.0~V < V_{BAT} < 4.5~V,~I_{LOAD}$ from 0 to 500 mA	4.77 5.07		5.20	V
IBAT(BOOST)	Boost Mode Quiescent Current	PFM Mode, V _{BAT} =3.6 V, I _{LOAD} =0		250	350	μA
I _{LIMPK(BST)}	Q2 Peak Current Limit		1350	1550	1950	mA
	Minimum Battery Voltage for Boost	While Boost Active		2.32		v
UVLO _{BST}	Operation	To Start Boost Regulator		2.48	2.70	v
VBUS Load	Resistance					
Р		Normal Operation		500		kΩ
R _{VBUS}	VBUS to PGND Resistance	VBUS Validation		100		Ω
Protection a	nd Timers					
VDUC	VBUS Over-Voltage Shutdown	V _{BUS} Rising	6.09	6.29	6.49	V
VBUS _{OVP}	Hysteresis	V _{BUS} Falling		100		mV
ILIMPK(CHG)	Q1 Cycle-by-Cycle Peak Current Limit	Charge Mode		3		А
V _{SHORT}	Battery Short-Circuit Threshold	V _{BAT} Rising	1.95	2.00	2.05	V
V SHORT	Hysteresis			100		mV
I _{SHORT}	Linear Charging Current	V _{BAT} < V _{SHORT} Power Path		13		mA
SHORT	Linear Ghaiging Guirent	Linear		30		
T _{SHUTDWN}	Thermal Shutdown Threshold ⁽⁷⁾	T _J Rising		145		°C
SHUTDWN	Hysteresis ⁽⁷⁾	T _J Falling		25		
T _{CF}	Thermal Regulation Threshold ⁽⁷⁾	Charge Current Reduction Begins		120		°C
t _{INT}	Detection Interval			2.1		s
t _{32S}	32-Second Timer ⁽⁸⁾	Charger Enabled		25.2	28.0	s
1325		Charger Disabled	18.0	25.2	34.0	3
t _{15MIN}	15-Minute Timer	15-Minute Mode (FAN54040, FAN54042, FAN54046, FAN54047)	12.0	13.5	15.0	min
Δt_{LF}	Low-Frequency Timer Accuracy	Charger Inactive	-25		25	%

Notes:

5. Negative current is current flowing from the battery to VBUS (discharging the battery).

6. Q2 always turns on for 60 ns, then turns off if current is below I_{SYNC}.

7. Guaranteed by design; not tested in production.

8. This tolerance (%) applies to all timers on the IC, including soft-start and deglitching timers.

I²C Timing Specifications

Guaranteed by design.

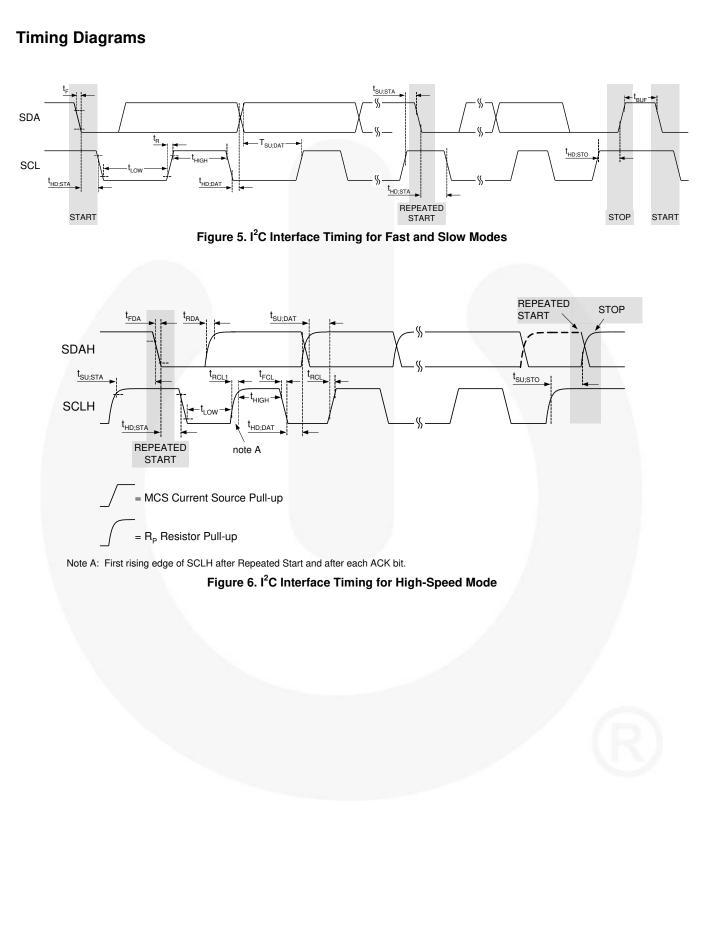
Symbol	Parameter	Conditions		Тур.	Max.	Uni		
		Standard Mode			100			
		Fast Mode			400			
f _{SCL}	SCL Clock Frequency	Fast Mode Plus			1000	kH		
		High-Speed Mode, C _B <u><</u> 100 pF			3400			
		High-Speed Mode, $C_B \leq 400 \text{ pF}$			1700			
		Standard Mode		4.7				
t _{BUF}	BUS-free Time between STOP and START Conditions	Fast Mode		1.3		μs		
		Fast Mode Plus		0.5				
		Standard Mode		4		μs		
+	START or Repeated START Hold	Fast Mode		600		ns		
t _{HD;STA} Time		Fast Mode Plus		260		ns		
		High-Speed Mode	1	160		ns		
		Standard Mode		4.7		μs		
	SCL LOW Period	Fast Mode		1.3		μs		
t _{LOW} S		Fast Mode Plus		0.5		μs		
		High-Speed Mode, $C_B \leq 100 \text{ pF}$		160	2	ns		
	1	High-Speed Mode, $C_B \leq 400 \text{ pF}$		320		ns		
		Standard Mode		4		μ		
		Fast Mode		600		ns		
t _{HIGH}	SCL HIGH Period	Fast Mode Plus		260		ns		
		High-Speed Mode, $C_B \le 100 \text{ pF}$		60		ns		
		High-Speed Mode, $C_B \leq 400 \text{ pF}$		120		ns		
		Standard Mode		4.7		μs		
	Demosted CTADT Catura Time	Fast Mode		600		ns		
tsu;sta	Repeated START Setup Time	Fast Mode Plus	1	260		ns		
		High-Speed Mode		160		ns		
		Standard Mode		250				
•	Data Satur Tima	Fast Mode		100				
t _{su;dat}	Data Setup Time	Fast Mode Plus		50		ns		
		High-Speed Mode		10				
		Standard Mode	0		3.45	με		
		Fast Mode	0		900	ns		
t _{HD;DAT}	Data Hold Time	Fast Mode Plus	0		450	ns		
		High-Speed Mode, $C_B \leq 100 \text{ pF}$	0		70	ns		
		High-Speed Mode, $C_B \le 400 \text{ pF}$	0		150	ns		
		Standard Mode	20+0	.1C _B	1000			
		Fast Mode	20+0.1C _B		300	I		
t _{RCL}	SCL Rise Time	Fast Mode Plus	20+0	.1C _B	120	ns		
		High-Speed Mode, $C_B \leq 100 \text{ pF}$		10	80			
		High-Speed Mode, C _B <u><</u> 400 pF		20	160			

Continued on the following page ...

I²C Timing Specifications (Continued)

Guaranteed by design.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit				
		Standard Mode	20+0.1C _B		300					
	SCL Fall Time	Fast Mode	20+0	.1C _B	300	ns				
t _{FCL}		Fast Mode Plus	20+0	.1C _B	120					
		High-Speed Mode, $C_B \leq 100 \text{ pF}$		10	40					
		High-Speed Mode, $C_B \leq 400 \text{ pF}$		20	80					
+	Rise Time of SCL after a Repeated	High-Speed Mode, $C_B \leq 100 \text{ pF}$		10	80	20				
t _{RCL1}	START Condition and after ACK Bit	High-Speed Mode, $C_B \leq 400 \text{ pF}$		20	160	ns				
		Standard Mode	20+0	1C _B	1000					
	SDA Rise Time	Fast Mode	20+0.	1C _B	300	ns				
t _{RDA}		Fast Mode Plus	20+0	.1C _B	120					
		High-Speed Mode, $C_B \leq 100 \text{ pF}$		10	80					
		High-Speed Mode, $C_B \leq 400 \text{ pF}$		20	160					
	1	Standard Mode	20+0	.1C _B	300					
		Fast Mode	20+0.1C _B		300	ns				
t _{FDA}	SDA Fall Time	Fast Mode Plus	20+0.	20+0.1C _B						
		High-Speed Mode, $C_B \leq 100 \text{ pF}$		10	80					
		High-Speed Mode, $C_B \leq 400 \text{ pF}$		20	160					
		Standard Mode		4		μS				
toward		Fast Mode		600		ns				
tsu;sто	Stop Condition Setup Time	Fast Mode Plus		120		ns				
		High-Speed Mode		160		ns				
CB	Capacitive Load for SDA and SCL				400	pF				



FAN54040 - FAN54047— USB-OTG,1.55 A Li-Ion Switching Charger with Power Path and 2.3 A Production Test Support



Charge Mode Typical Characteristics

Unless otherwise specified, circuit of Figure 1, V_{OREG} =4.2 V, V_{BUS} =5.0 V, and T_A =25°C.

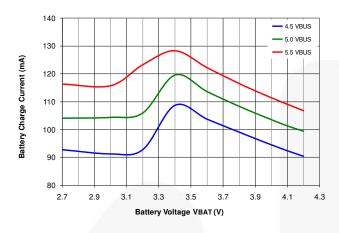
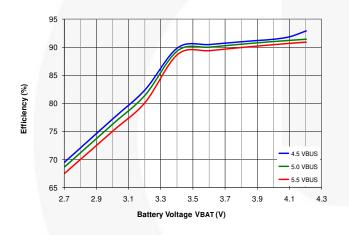
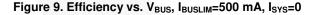


Figure 7. Battery Charge Current vs. V_{BUS} with $I_{\text{BUSLIM}}{=}100\mbox{ mA}$





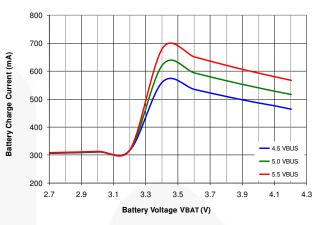
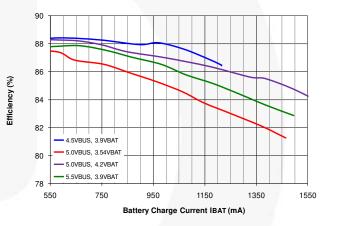
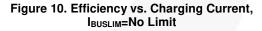
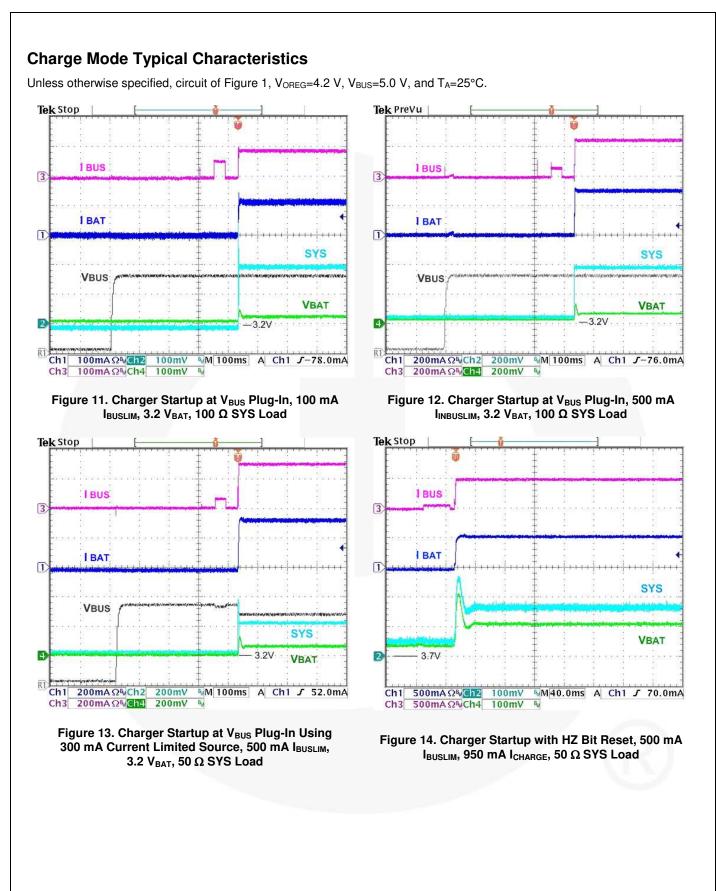
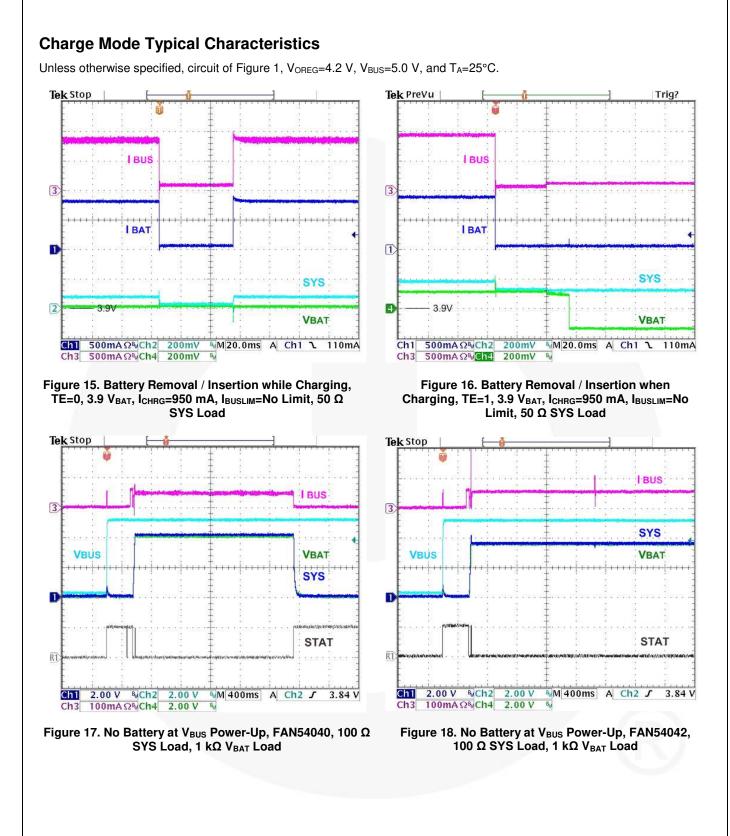


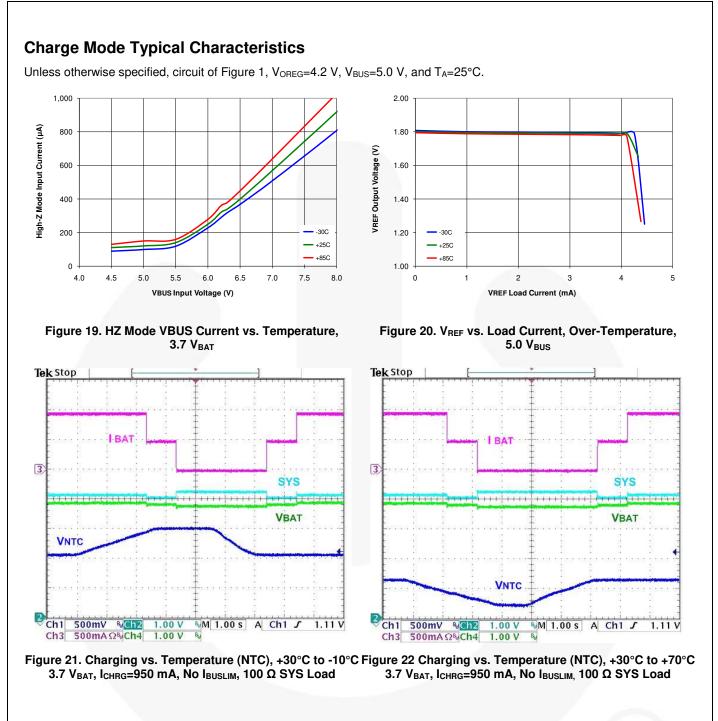
Figure 8. Battery Charge Current vs. V_{BUS} with $I_{\text{BUSLIM}}{=}500\mbox{ mA}$











GSM Typical Characteristics

A 2.0 A GSM pulse applied at VBAT with 5 μs rise / fall time. Simultaneous to GSM pulse, 50 Ω additional load applied at SYS.

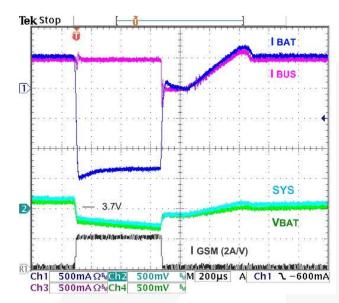
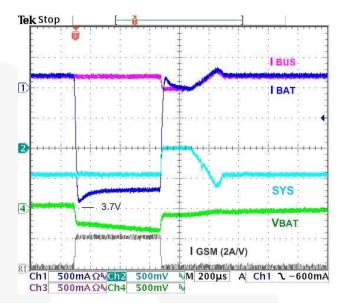
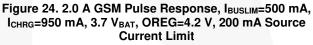
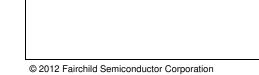


Figure 23. 2.0 A GSM Pulse Response, I_{BUSLIM}=500 mA Control, I_{CHRG}=950 mA, 3.7 V_{BAT}, OREG=4.2 V

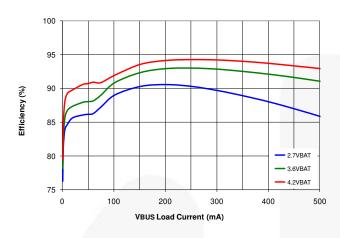






Boost Mode Typical Characteristics

Unless otherwise specified, using circuit of Figure 1, V_{BAT} =3.6 V, T_A =25°C.



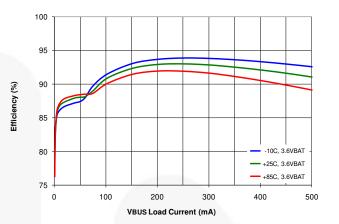


Figure 25. Efficiency vs. IBUS Over VBAT

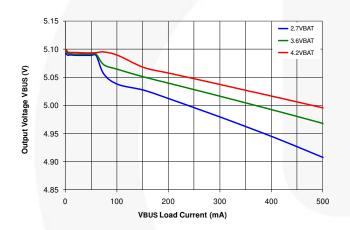


Figure 27. Regulation vs. IBUS Over VBAT

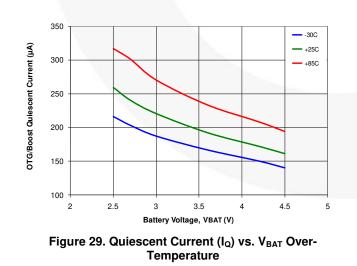


Figure 26. Efficiency vs. IBUS Over-Temperature, 3.6 VBAT

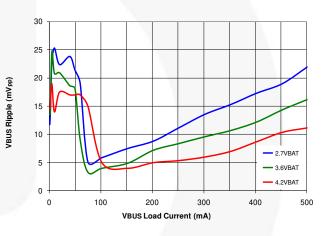
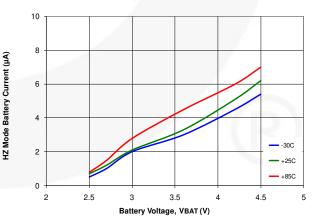


Figure 28. Output Ripple vs. IBUS Over VBAT

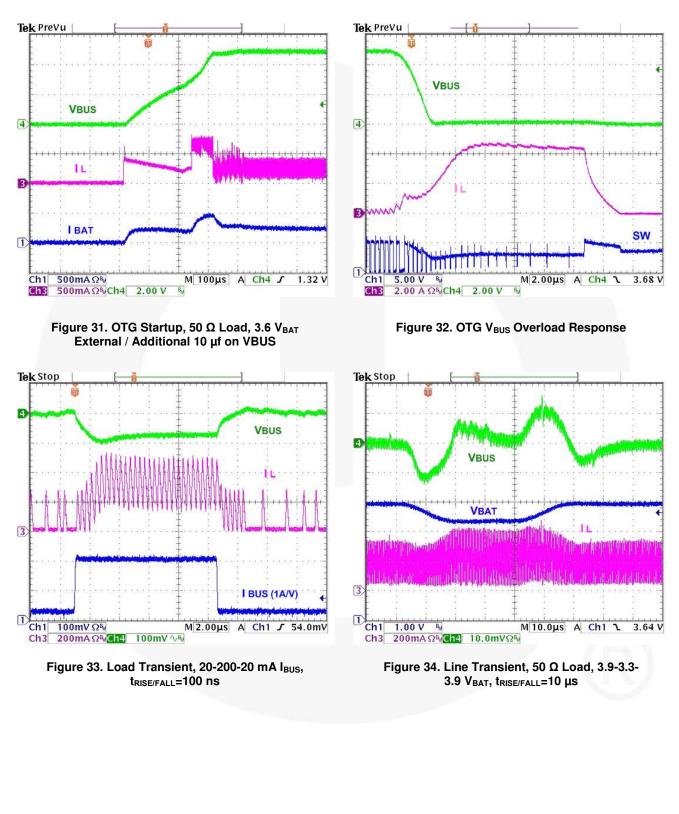






Boost Mode Typical Characteristics

Unless otherwise specified, using circuit of Figure 1, V_{BAT}=3.6 V, T_A=25°C.



Circuit Description / Overview

When charging batteries with a current-limited input source, such as USB, a switching charger's high efficiency over a wide range of output voltages minimizes charging time.

FAN5404X combines a highly integrated synchronous buck regulator for charging with a synchronous boost regulator, which can supply 5 V to USB On-The-Go (OTG) peripherals. The FAN5404X employs synchronous rectification for both the charger and boost regulators to maintain high efficiency over a wide range of battery voltages and charge states.

The FAN5404X has four operating modes:

- 1. Charge Mode: Charges a single-cell Li-ion or Li-polymer battery.
- Boost Mode: Provides 5 V power to USB-OTG with an integrated synchronous rectification boost regulator, using the battery as input.
- High-Impedance Mode: Both the boost and charging circuits are OFF in this mode. Current flow from VBUS to the battery or from the battery to VBUS is blocked in this mode. This mode consumes very little current from VBUS or the battery.
- 4. Production Test Mode This mode provides 4.2 V output on VBAT and supplies a load current of up to 2.3 A.

Charge Mode

In Charge Mode, FAN5404X employs six regulation loops:

- 1. Input Current: Limits the amount of current drawn from VBUS. This current is sensed internally and can be programmed through the I²C interface.
- Charging Current: Limits the maximum charging current. This current is sensed using an internal sense MOSFET.
- VBUS Voltage: This loop is designed to prevent the input supply from being dragged below V_{BUSLIM} (typically 4.5 V) when the input power source is current limited. An example of this would be a travel charger. This loop cuts back the current when V_{BUS} approaches V_{BUSLIM}, allowing the input source to run in current limit.
- 4. Charge Voltage: The regulator is restricted from exceeding this voltage. As the internal battery voltage rises, the battery's internal impedance works in conjunction with the charge voltage regulation to decrease the amount of current flowing to the battery. Battery charging is completed when the current through Q4 drops below the I_{TERM} threshold.
- 5. Power Path: When V_{BAT} is below V_{BATMIN} , Q4 operates as a linear current source and modulates its current to ensure that the voltage on SYS stays above 3.4 V.
- Temperature: If the IC's junction temperature reaches 120°C, charge current is reduced until the IC's temperature is below 120°C.

Battery Charging Curve

If the battery voltage is below V_{SHORT}, a linear current source pre-charges the battery until V_{BAT} reaches V_{SHORT}. The PWM charging circuit is then started and the battery is charged with a constant current if sufficient input power is available. The current slew rate is limited to prevent overshoot.

The FAN5404X is designed to work with a current-limited input source at VBUS. During the current regulation phase of charging, I_{BUSLIM} or the programmed charging current limits the amount of current available to charge the battery and power the system. The effect of I_{BUSLIM} on I_{CHARGE} can be seen in Figure 36.

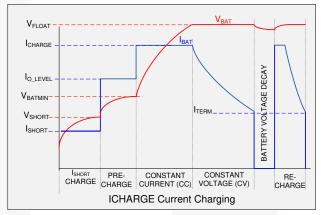


Figure 35. Charge Curve, ICHARGE Not Limited by IINLIM

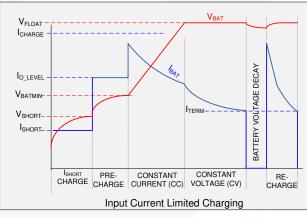


Figure 36. Charge Curve, IBUSLIM Limits ICHARGE

Assuming that V_{OREG} is programmed to the cell's fully charged "float" voltage, the current that the battery accepts with the PWM regulator limiting its output (sensed at VBAT) to V_{OREG} declines and the charger enters the voltage regulation phase of charging. When the current declines to the programmed I_{TERM} value, the charge cycle is complete. Charge current termination can be disabled by resetting the TE bit (REG1[3]).

The charger output or "float" voltage can be programmed by the OREG bits from 3.5 V to 4.44 V in 20 mV increments, as shown in Table 4.

The following charging parameters can be programmed by the host through $I^2 C\colon$

Parameter	Name	Register					
Output Voltage Regulation	VOREG	REG2[7:2]					
Battery Charging Current Limit	I _{OCHRG}	REG4[6:3]					
Input Current Limit	I _{INLIM}	REG1[7:6]					
Charge Termination Limit	I _{TERM}	REG4[2:0]					
Weak Battery Voltage	V_{LOWV}	REG1[5:4]					

Table 3. Programmable Charging Parameters

Table 4. OREG Bits (OREG[7:2]) vs. Charger V_{OUT} (V_{OREG}) Float Voltage

Decimal	Hex	VOREG	Decimal	Hex	VOREG
0	00	3.50	24	18	3.98
1	01	3.52	25	19	4.00
2	02	3.54	26	1A	4.02
3	03	3.56	27	1B	4.04
4	04	3.58	28	1C	4.06
5	05	3.60	29	1D	4.08
6	06	3.62	30	1E	4.10
7	07	3.64	31	1F	4.12
8	08	3.66	32	20	4.14
9	09	3.68	33	21	4.16
10	0A	3.70	34	22	4.18
11	0B	3.72	35	23	4.20
12	0C	3.74	36	24	4.22
13	0D	3.76	37	25	4.24
14	0E	3.78	38	26	4.26
15	0F	3.80	39	27	4.28
16	10	3.82	40	28	4.30
17	11	3.84	41	29	4.32
18	12	3.86	42	2A	4.34
19	13	3.88	43	2B	4.36
20	14	3.90	44	2C	4.38
21	15	3.92	45	2D	4.40
22	16	3.94	46	2E	4.42
23	17	3.96	47 - 63	2F-3F	4.44

Note:

9. Default settings are denoted by **bold** typeface.

Provided DIS, CE# and HZ_MODE are LOW, a new charge cycle begins when one of the following occurs:

- 1. The battery voltage falls below V_{OREG} V_{RCH} after charge termination has occurred.
- 2. Any I^2C write occurs causing the T32 s timer to run.

Products that include the auto-charge feature also begin charging if:

3. VBUS Power-on-Reset (POR) occurs and the battery voltage is below the weak battery threshold (V_{LOWV}).

Charge Current Limit (IOCHARGE)

Table 5. $I_{OCHARGE}$ Current as Function of $I_{OCHARGE}$ Bits (REG4 [6:3])

DEC	BIN	HEX	I _{OCHARGE} (mA)
0	0000	0	550
1	0001	1	650
2	0010	2	750
3	0011	3	850
4	0100	4	950
5	0101	5	1,050
6	0110	6	1,150
7	0111	7	1,250
8	1000	8	1,350
9	1001	9	1,450
10-15	1010-1111	A-F	1,550

When the IO_LEVEL bit is set (default), the $I_{\rm OCHARGE}$ bits are ignored and charge current is set to 340 mA.

PWM Controller in Charge Mode

The IC uses a current-mode PWM controller to regulate the output voltage and battery charge currents. The synchronous rectifier (Q2) has a negative current limit that turns off Q2 at 140 mA to prevent current flow from the battery.

Termination Current Limit

Current charge termination is enabled when TE (REG1[3])=1. Typical termination current values are given in Table 6.

Table 6. Termination Current as Function of ITERM Bits (REG4[2:0]) or PC IT Bits (REG7[2:0]

ITERM Bits or PC_IT Bits	Termination Current (mA)
0	50
1	100
2	150
3	200
4	250
5	300
6	350
7	400

When the charge current falls below I_{TERM} PWM charging stops, but the STAT pin remains LOW. The STAT pin then goes HIGH and the STATUS bits change to CHARGE DONE (10), provided the battery and charger are still connected.

A post-charging feature, "top-off" charging, is available to continue the battery charging to a lower charge current to maximize battery capacity. The PC_EN bit must be set to 1 before the battery charging current reaches the termination current I_{TERM} for normal charging. The post-charging termination current is set by the PC_IT[2:0] bits, as shown in Table 6. If PC_EN is set to 1; right after the normal charging is ended as described above, post charging is started with PC_ON monitor bit set to 1. Once the current reaches the

threshold for post-charging completion, PWM charging stops and PC_ON bit changes back to 0.

During post-charging, the STAT pin is HIGH, indicating that the charge current is below the $I_{\rm TERM}$ level. To exit post-charging, one of the following must occur: a $V_{\rm BUS}$ POR, the POK_B cycled when $V_{\rm BAT}$ <3.0 V, or the CE# or HZ_Mode bit cycled.

Safety Timer

At the beginning of charging, the IC starts a 15-minute timer (t_{15MIN}). When this timer times out, charging is terminated. Writing to any register through I²C stops and resets the t_{15MIN} timer, which in turn starts a 32-second timer (t_{32S}). Setting the TMR_RST bit (REG0[7]) resets the t_{32S} timer. If the t_{32S} timer times out; charging is terminated, the registers are set to their default values, and charging resumes using the default values with the t_{15MIN} timer running.

Normal charging is controlled by the host with the t_{32S} timer running to ensure that the host is alive. Charging with the $t_{15\text{MIN}}$ timer running is used for charging unattended by the host. If the $t_{15\text{MIN}}$ timer expires, the IC turns off the charger and indicates a timer fault (110) on the FAULT bits (REG0[2:0]). This sequence prevents overcharge if the host fails to reset the t_{32S} timer.

V_{BUS} POR / Non-Compliant Charger Rejection

256 ms after VBUS is connected, the IC pulses the STAT pin and sets the VBUS_CON bit. Before starting to supply current, the IC applies a 110 Ω load from VBUS to GND. V_{BUS} must remain above V_{IN(MIN)1} and below VBUS_{OVP} for t_{VBUS_VALID} (32 ms) before the IC initiates charging or supplies power to SYS. The V_{BUS} validation sequence always occurs before significant current is drawn from VBUS (for example, after a VBUS OVP fault or a V_{RCH} recharge initiation). t_{VBUS_VALID} ensures that unfiltered 50/60 Hz chargers and other non-compliant chargers are rejected.

USB-Friendly Boot Sequence

At V_{BUS} POR, when the battery voltage is above the weak battery threshold (V_{LOWV}); the IC operates in accordance with its I^2C register settings. If V_{BAT} < V_{LOWV} and t_{32s} is not running, the IC sets all registers to their default values and begins to deliver power to SYS.

FAN54040, FAN54042, and FAN54047 feature auto-charge, which allow these parts to deliver charge to the battery prior to receiving host commands.

FAN54041 does not automatically initiate charging at V_{BUS} POR. Instead, it waits in IDLE state for the host to initiate charging through I^2C commands. While in IDLE state, Q4 and Q5 are on. This allows the system to run through a separate power path without requiring an additional disconnection MOSFET.

Power Path Operation

As long as $V_{BAT} < V_{BATMIN}$, Q4 operates as a linear current source, (Power Path Mode) with its current limited to 340 mA. The IC then regulates SYS to 3.54 V and attempts to charge the battery with as much current as possible with the available I_{BUSLIM} input current, without allowing SYS to drop below 3.4 V. This ensures that system power always receives first priority from a limited input supply. During this

time, POK_B is HIGH. If V_{BAT} < V_{SHORT}, Q4's current is further reduced to about 13 mA (I_{SHORT}) when I_{BUSLIM} is set to 100 or 500 mA. For all other input current limits, I_{SHORT} current is approximately 30 mA.

The POK_B signal can be used to keep the system in a lowpower state, preventing excessive loading from the system while attempting to charge a depleted battery.

Table 7. VBATMIN Thresholds to Exit Power Path Mode

I _{BUSLIM} (mA)	V _{BATMIN} (V)
100	3.4
500	3.3
800	3.2
No Limit	3.2

After V_{BAT} reaches $V_{BATMIN},\ Q4$ closes and is used as a current-sense element to limit I_{CHARGE} per the I^2C register settings by limiting the PWM modulator's current (Full PWM Mode). During PWM Mode, if SYS drops more than 5 mV (V_{THSYS}) below $V_{BAT},\ Q4$ and Q5 are turned on (GATE is pulled LOW). Once SYS voltage becomes higher than $V_{BAT},\ Q5$ is turned off and Q4 again serves as the current-sense element to limit $I_{OCHARGE}.$

Q4 and Q5 are both turned on when the IC enters SLEEP Mode (V_{BUS} < V_{BAT}).

POK_B pulls LOW once V_{BAT} reaches V_{LOWV} , and remains LOW as long as the IC is in Full PWM Mode. The IC remains in Full PWM Mode as long as V_{BAT} > 3.0 V, at which point, the IC enters Power Path Charging Mode.

Startup with a Dead Battery

At V_{BUS} POR, a 2 k Ω load is applied to VBAT for 256 ms to discharge any residual system capacitance in case the battery is absent or its discharge protection switch is open.

If V_{BAT} < V_{LOWV} , all registers are reset to default values and the IC charges in T15Min Mode. If V_{BAT} < V_{SHORT} , the SAFETY register is reset to its default value and the Battery Detection test below is performed.

Battery Detection

If V_{BAT} is below V_{SHORT} when charging is enabled, the DBAT_B bit is reset and the IC (except FAN54045 and FAN54046) performs an addition battery detection test.

After V_{BAT} rises above V_{SHORT}, PWM charging begins (when CE# = 0) with the float voltage (V_{OREG}) temporarily set to 4 V. If the battery voltage exceeds 3.7 V within 32 ms of the beginning of PWM charging, the battery is absent. If battery absence is detected:

- 1. STAT pulses, with FAULT bits set to 111, and the NOBAT bit is set.
- 2. For FAN54040 only; the t_{15MIN} timer is disabled until V_{BUS} is removed, IDLE state is entered, and POK_B remains HIGH.
- 3. The IC bypasses the protection switch close test below, since no battery is present.

The FAN54042 and FAN54047 continue to charge.

If V_{BAT} remained below 3.7 V during the initial 32 ms period, Power Path Mode charging continues to ensure that the

battery's discharge protection switch has closed before exiting Power Path Mode:

- 1. If V_{BAT} is less than 3.4 V, V_{SYS} is set to 4 V, and Power Path charging continues until V_{BAT} has exceeded 3.4 V for at least 128 ms. Charging continues until:
- 2. V_{BAT} has dropped below 3.2 V for at least 32 ms. Once this occurs, V_{SYS} returns to the OREG register setting (default 3.54 V).
- 3. V_{BAT} has again risen above V_{BATMIN} for at least 4 ms.

After these three events, PWM Mode is entered and the IC sets the DBAT_B bit. If the host sets the DBAT_B bit (Reg2[1]), events 1 and 2 above are skipped and PWM Mode is entered once V_{BAT} rises above V_{BATMIN} .

In a typical application, as soon as the host processor has cleared its UVLO threshold (typically 3.3 V), the host's low level software would set the IBUSLIM and IOCHARGE registers to charge the battery more rapidly above V_{BATMIN} as soon as the host determines that more than 100 mA is available through VBUS (see Figure 37).

Once the host processor begins writing to the IC, charge parameters are set by the host, which must continually reset the t_{32S} timer to continue charging using the programmed charging parameters.

If t_{32S} times out; the register defaults are loaded, the FAULT bits are set to 110, STAT is pulsed, and charging continues with default charge parameters in T15MIN Mode for the FAN54040, FAN54042, and FAN54047.

POK_B (see Table 8)

The POK_B pin and bit are intended to provide feedback to the baseband processor that the battery is strong enough to allow the device to fully function. Whenever the IC is operating in Power Path Mode, POK_B is HIGH. On exiting Power Path Mode, POK_B remains HIGH until V_{BAT} > V_{LOWV}. Reg1[5:4] sets the V_{LOWV} threshold.

The STAT pin pulses any time the POK_B pin changes.

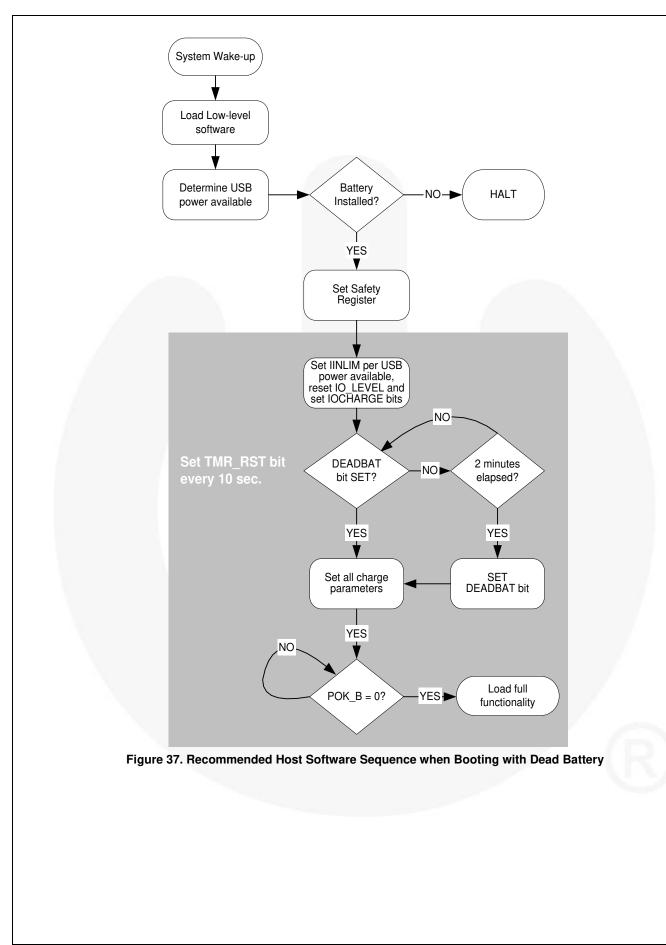
Table 8 Q4	Q5 POK	B and	GATE On	eration vs	Charging Mode
		. D , анс		ciation vs.	Charging Mode

Q4 CC-CV Control	V _{BUS}	V _{BAT}	V _{SYS}	Q4	Q5	GATE	POK_B
Power Path Mode: Maintain $V_{SYS} \ge 3.4 V$	Valid	< V _{BATMIN}	<u><</u> 3.4	Linear	OFF	HIGH	HIGH
Power Path Mode: Limit I _{CHARGE} < 340 mA	Valid	< V _{BATMIN}	> 3.4	Linear	OFF	HIGH	HIGH
DWM Made Of Sanage Current for L	Valid	$> V_{BATMIN}$ and $< V_{LOWV}$	v			HIGH	HIGH
PWM Mode. Q4 Senses Current for I _{CHARGE}	Valid	> V _{LOWV}		ON	OFF		LOW
OFF	<v<sub>BAT</v<sub>	Х	Х	ON	ON	LOW	HIGH

Note:

10. POK_B remains LOW until Q4 returns to Power Path Mode. Q4 and Q5 are both ON if $V_{SYS} < V_{BAT}$ and CE# = 0. If CE# = 1 and $V_{SYS} < V_{BAT}$, Q5 is OFF and Q4 blocks current flow from VBAT to SYS.

	· ·				JAI		
PWM	Charger	CE#	V _{BUS}	V _{BAT}	Q4	Q5	GATE
ON	PWM Mode	0	Valid	< V _{SYS} , >V _{BATMIN}	ON	OFF	HIGH
ON	PWM Mode	0	Valid	> V _{SYS} , >V _{BATMIN}	ON	ON	LOW
ON	Disabled	1	Valid	Х	OFF	OFF	HIGH
ON	Power Path Charging	0	Valid	2 V < V _{BAT} < V _{BATMIN}	Linear	OFF	HIGH
OFF	30 mA Linear Charging	Х	Valid	$< 2 V_{BAT}$	ON	ON	LOW
OFF	OFF	Х	Х	Х	ON	ON	LOW



Battery Temperature (NTC) Monitor

The FAN5404X reduces the maximum charge current and termination voltage if an NTC measuring battery temperature (T_{BAT}) indicates that it is outside the fast-charging limits (T2 to T3), as described in the JEITA specification¹. There are four temperature thresholds that change battery charger operation: T1, T2, T3, and T4, shown in Table 10.

Table 10. Battery Temperature Thresholds

		· · · · · ·	D (0) 0
For use with	$10 \text{ k}\Omega \text{ NIC},$	B = 3380, and	$R_{REF} = 10 k\Omega$.

Threshold	Temperature	% of V _{REF}	
T1	0°C	73.9	
T2	10°C	64.6	
Т3	45°C	32.9	
T4	60°C	23.3	

Table 11. Charge Parameters vs. T_{BAT}

Т _{ват} (°С)	I _{CHARGE}	V _{FLOAT}	
Below T1	Charging to VBAT Disabled		
Between T1 and T2	I _{OCHARGE} / 2 ⁽¹¹⁾	4.0 V	
Between T2 and T3	IOCHARGE	V _{OREG}	
Between T3 and T4	I _{OCHARGE} / 2 ⁽¹¹⁾	4.0 V	
Above T4	Charging to VBAT Disabled		

Note:

11. If I_{OCHARGE} is programmed to less than 650 mA, the charge current is limited to 340 mA.

Thermistors with other β values can be used, with some shift in the corresponding temperature threshold, as shown in Table 12.

Table 12. Thermistor Temperature Thresholds

R_{REF} = R_{THRM} at 25°C

Parameter	Various Thermistors			
R _{THRM(25°C)}	10 kΩ	10 kΩ	47 kΩ	100 kΩ
β	3380	3940	4050	4250
T1	0°C	3°C	6	8
T2	10°C	12°C	13	14
Т3	45°C	42°C	41	40
T4	60°C	55°C	53	51

¹ Japan Electronics and Information Technology Industries Association (JEITA) and Battery Association of Japan. "A Guide to the Safe Use of Secondary Lithium Ion Batteries in Notebook-type Personal Computers," April 28, 2007. The host processor can disable temperature-driven control of charging parameters by writing 1 to the TEMP_DIS bit. Since TEMP_DIS is reset whenever the IC resets its registers, the temperature controls are enforced whenever the IC is auto-charging, since auto-charge is always preceeded by a reset of registers.

To disable the thermistor circuit, tie the NTC pin to GND. Before enabling the charger, the IC tests to see if NTC is shorted to GND. If NTC is shorted to GND, no thermistor readings occur and the NTC_OK and NTC1-NTC4 is reset.

The IC first measures the NTC immediately prior to entering any PWM charging state, then measures the NTC once per second, updating the result in NTC1-NTC4 bits (Reg 12H[3:0]).

Table 13. NTC1-NTC4 Decoding

T _{BAT} (°C)	NTC4	NTC3	NTC2	NTC1
Above T4	1	1	1	1
Between T3 and T4	0	1	1	1
Between T2 and T3	0	0	1	1
Between T1 and T2	0	0	0	1
Below T1	0	0	0	0